



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

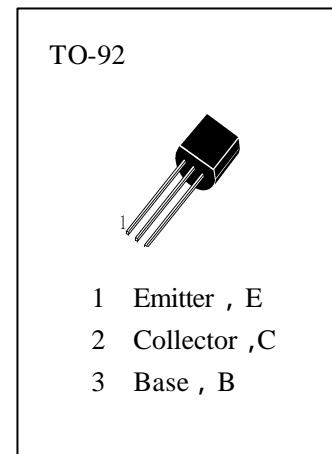
H3200

APPLICATIONS

Low Noise Audio Amplifier Application

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation.....	300mW
V_{CBO} —Collector-Base Voltage.....	120V
V_{CEO} —Collector-Emitter Voltage.....	120V
V_{EBO} —Emitter-Base Voltage.....	5V
I_c —Collector Current.....	100mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage	120			V	$I_C=1\text{mA}, I_B=0$
ICBO	Collector Cut-off Current			100	nA	$V_{CB}=120\text{V}, I_E=0$
IEBO	Emitter Cut-off Current			100	nA	$V_{EB}=5\text{V}, I_C=0$
HFE	DC Current Gain	200		700		$V_{CE}=6\text{V}, I_C=2\text{mA}$
VCE(sat)	Collector- Emitter Saturation Voltage			0.3	V	$I_C=10\text{mA}, I_B=1\text{mA}$
VBE(ON)	Base-Emitter On Voltage		0.65		V	$V_{CE}=6\text{V}, I_C=2\text{mA}$
f _T	Current Gain- Bandwidth Product		100		MHz	$V_{CE}=6\text{V}, I_C=1\text{mA}$
C _{ob}	Output Capacitance		3.0		pF	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$
NF	Noise Figure			6	dB	$V_{CE}=6\text{V}, I_C=100 \mu\text{A}$ $f=10\text{KHz}, R_g=10\text{K}$
NF				2	dB	$V_{CE}=6\text{V}, I_C=100 \mu\text{A}$ $f=1\text{KHz}, R_g=10\text{K}$
NF			3		dB	$V_{CE}=6\text{V}, I_C=100 \mu\text{A}$ $f=1\text{KHz}, R_g=100\text{K}$

h_{FE} Classification

GR**BL**

200—400

350—700



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